

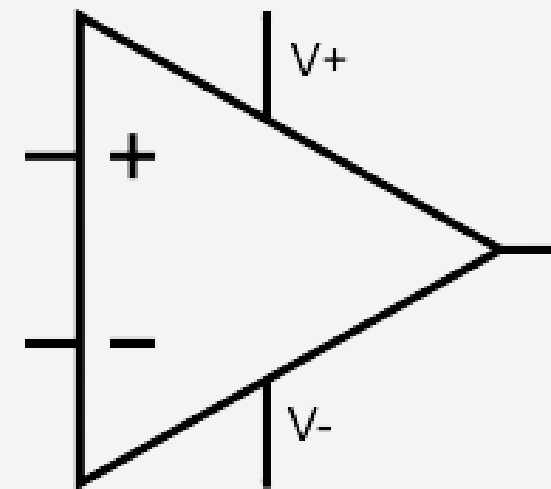
DIFFERENTIAL AMPLIFIER

NASCENT SEMICONDUCTOR JFET DIFFERENTIAL AMPLIFIER

High reliability, high temperature, radiation tolerant differential amplifiers based on depletion mode silicon carbide n-channel junction FETs in hermetic sealed packaging. Optimised for signal level applications in extreme environments.

FEATURES

- Differential input
- Non-inverting output
- Low input capacitance
- Minimum operating voltage +/- 12 V
- Maximum operating temperature 400°C
- Maximum Total Ionising Dose in excess of 250 krad



RATINGS

25 °C Operation	Minimum	Typical	Maximum	Units
Open Loop Gain- Single Stage		250		
Open Loops Gain - Three Stage		1500		
Phase Shift - Three Stage			5	°
Input Impedance	1			TOhm
Output Impedance			10	kOhm
Input Capacitance			10	pF
Eviquivalent Noise			0.01	fA ² /Hz

400 °C Operation	Minimum	Typical	Maximum	Units
Open Loop Gain- Single Stage		55		
Open Loops Gain - Three Stage		200		
Phase Shift - Three Stage			8	°
Input Impedance	0.1			TOhm
Output Impedance			18	kOhm
Input Capacitance			10	pF
Eviquivalent Noise			0.05	fA ² /Hz

PART NUMBER LJDA-0150
JFET DIFFERENTIAL AMPLIFIER



Nascent Semiconductor Limited
Salvus House, Aykley Heads, Durham, DH1 5TS
www.nascentsemi.com
+44 (0)7738 242517
info@nascentsemi.com